

TENTATIVE

TOSHIBA GATE TURN-OFF THYRISTOR

SG800GXH25

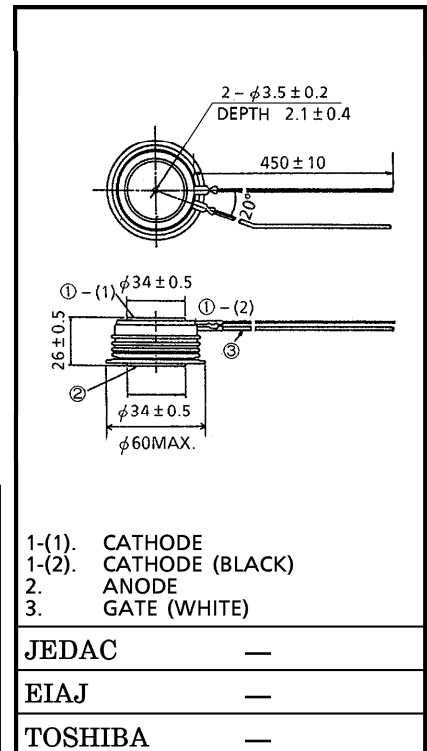
INVERTER APPLICATION

Unit in mm

- Repetitive Peak Off-State Voltage : $V_{DRM} = 4500\text{ V}$
(Note 1)
- Repetitive Peak Reverse Voltage : $V_{RRM} = 4000\text{ V}$
- R.M.S On-State Current : $I_T(\text{RMS}) = 300\text{ A}$
- Peak Turn-Off Current : $I_{TGQM} = 800\text{ A}$
- Critical Rate of Rise of On-State Current : $di/dt = 200\text{ A}/\mu\text{s}$
- Critical Rate of Rise of Off-State Voltage : $dv/dt = 900\text{ V}/\mu\text{s}$

MAXIMUM RATINGS

CHARACTERISTIC	SYMBOL	RATING	UNIT
Repetitive Peak Off-State Voltage (Note 1)	V_{DRM}	4500	V
Repetitive Peak Reverse Voltage	V_{RRM}	4000	V
Peak Turn-Off Current (Note 2)	I_{TGQM}	800	A
R.M.S On-State Current (Note 3)	$I_T(\text{RMS})$	300	A
Peak One Cycle Surge On-State Current (Non Repetitive, 10 ms- Width Half Sine Waveform)	I_{TSM}	4000 (50 Hz) 4400 (60 Hz)	A
Critical Rate of Rise of On-State Current (Note 4)	di/dt	200	A / μs
Peak Forward Gate Current	I_{FGM}	40	A
Average Gate Power Dissipation	$P_G(\text{AV})$	80	W
R.M.S Gate Current (Note 5)	$I_G(\text{RMS})$	42	A
Peak Reverse Gate Voltage (At Static)	V_{RGM}	15	V
Operation Junction Temperature Range	T_j	-40~115	°C
Storage Temperature Range	T_{stg}	-40~115	°C
Mounting Force	—	11.8 ± 1.2	kN



- 1-(1). CATHODE
- 1-(2). CATHODE (BLACK)
- 2. ANODE
- 3. GATE (WHITE)

JEDAC —

EIAJ —

TOSHIBA —

Weight : 460 g

(Note 1) : $V_{GK} = -2\text{ V}$

(Note 2) : $V_D = 2400\text{ V}$, $V_{DM} \leq 3000\text{ V}$, $C_S \geq 2\ \mu\text{F}$, $di_{GQ}/dt \geq 25\text{ A}/\mu\text{s}$, $V_{DSP} \leq 600\text{ V}$,
 $L_S \leq 0.2\ \mu\text{H}$ (TOSHIBA METHOD)

(Note 3) : 50 Hz Half Sine Waveform

(Note 4) : $V_D \leq 2400\text{ V}$, $I_{TM} \leq 800\text{ A}$, $I_G \geq 12\text{ A}$ ($t_r \leq 1\ \mu\text{s}$), $f \leq 50\text{ Hz}$, $C_S \leq 2\ \mu\text{F}$,
 $R_S \geq 10\ \Omega$, $25^\circ\text{C} \leq T_j \leq 115^\circ\text{C}$

(Note 5) : Ambient Temperature of coaxial gate-cathode lead = 90°C

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ELECTRICAL CHARACTERISTICS

CHARACTERISTIC	SYMBOL	TEST CONDITION	MIN	TYP.	MAX	UNIT	
Repetitive Peak Off-State Current	I_{DRM}	$V_{DRM} = 4500 \text{ V}$, $V_{GK} = -2 \text{ V}$ $T_j = 115^\circ\text{C}$	—	—	50	mA	
Repetitive Peak Reverse Current	I_{RRM}	$V_{RRM} = 4000 \text{ V}$ $T_j = 115^\circ\text{C}$	—	—	50	mA	
Repetitive Peak Reverse Gate Current	I_{RGM}	$V_{RGM} = 15 \text{ V}$ $T_j = 115^\circ\text{C}$	—	—	10	mA	
Peak On-State Voltage	V_{TM}	$I_{TM} = 800 \text{ A}$, $T_j = 115^\circ\text{C}$	—	—	4.7	V	
Gate Trigger Voltage	V_{GT}	$V_D = 24 \text{ V}$	$T_j = -40^\circ\text{C}$	—	—	1.7	V
			$T_j = 25^\circ\text{C}$	—	—	1.2	V
Gate Trigger Current	I_{GT}	$R_L = 0.2 \Omega$	$T_j = -40^\circ\text{C}$	—	—	4.0	A
			$T_j = 25^\circ\text{C}$	—	—	1.0	A
Turn-On Delay Time	t_d	$V_D = 2250 \text{ V}$, $I_{TM} = 800 \text{ A}$ $di_F/dt = 200 \text{ A}/\mu\text{s}$	—	—	2.0	μs	
Turn-On Time	t_{gt}	$I_{GM} = 12 \text{ A}$ ($t_r = 1 \mu\text{s}$) $T_j = 25^\circ\text{C}$, non-snubber	—	—	8.0	μs	
Critical Rate of Rise of Off-State Voltage	dv/dt	$V_{DRM} = 3000 \text{ V}$ $T_j = 115^\circ\text{C}$, $V_{GK} = -4 \text{ V}$ Exponential Rise	900	—	—	$\text{V}/\mu\text{s}$	
Storage Time	t_s	$I_{TGQ} = 800 \text{ A}$	—	—	16	μs	
Gate Turn-Off Time	t_{gq}	$V_{DM} = 3000 \text{ V}$, $T_j = 115^\circ\text{C}$	—	—	18	μs	
Tail Time	t_{tail}	$V_D = 2250 \text{ V}$, $C_S = 2 \mu\text{F}$ $di_{GQ}/dt = 25 \text{ A}/\mu\text{s}$	—	—	200	μs	
Gate Turn-Off Current	I_{GQ}	Off squeeze current $\geq 300 \text{ mA}$	—	—	300	A	
Reverse Recovery Charge	Q_{rr}	$I_T = 800 \text{ A}$, $V_R = 1500 \text{ V}$ $C_S = 2 \mu\text{F}$, $R_S = 20 \Omega$	—	—	2500	μC	
Reverse Recovery Time	t_{rr}	$di_T/dt = -100 \text{ A}/\mu\text{s}$ $T_j = 115^\circ\text{C}$	—	—	10	μs	
Thermal Resistance	$R_{th(j-f)}$	Junction to fin	—	—	0.045	$^\circ\text{C}/\text{W}$	

